FULLY SALICIDED (FUSA) MOSFET STRUCTURE

FIELD OF THE INVENTION

The present invention relates to a MOSFET structure design and fabrication process and in particular to a MOSFET device with planarized gate and source/drain (S/D) regions wherein the gate and S/D regions are self-aligned, fully silicided, and have silicidation stoppers which are a gate dielectric layer and metallic barrier, respectively.

BACKGROUND OF THE INVENTION

The demand for greater circuit density and higher performance in Complementary Metal Oxide Semiconductor (CMOS) transistors is driving the critical gate dimension to 65 nm and below. For MOS-based IC manufacturing, a polysilicon gate has been used for many generations in spite of some shortcomings that include the well known poly-depletion effect which was first recognized over 10 years ago. The continued miniaturization of MOS Field Effect Transistor (MOSFET) devices and associated demand for better channel electrostatic control, higher gate capacitance, and higher drive current means that the gate dielectric thickness needs to be scaled down aggressively. For the 65 nm technology node and beyond, the equivalent electrical gate oxide thickness (EOT) must be thinned to below 15 Angstroms. Since poly-depletion has consistently contributed 4 to 10 Angstroms to the total EOT, the poly-depletion effect is no longer acceptable, regardless of advancements made on the high k dielectric layer between the gate and channel. To reduce the high gate resistance and poly-depletion problems, the active dopant density in the polysilicon gate must be increased. However, this practice leads to carrier mobility degradation. Thus, a

considerable amount of research and development effort is taking place to identify an alternative gate electrode such as a metal electrode that is much more conductive than conventional heavily doped polysilicon gates and is free of the poly-depletion issue.

Many types of metal electrodes and associated schemes have been investigated. Examples of conductive materials used in metal gate technology are metals such as W and Mo, metal silicides including nickel silicide and cobalt silicide, and metallic nitrides such as TiN and WN. An important requirement for a gate electrode is its capability of having a tunable work function (Φ_m) around its mid-gap so that the threshold voltage (Vth) for NMOS and PMOS devices can be obtained symmetrically. One attractive approach for implementing a metal gate in a transistor device is to employ a silicidation process that completely consumes a conventional polysilicon gate electrode which is converted to a silicide. A metal gate formed through the process of silicidation and referred to as a Fully Silicided (FUSI) poly gate is a strong contender for gate electrode in advanced technologies because an n-type or p-type dopant that is implanted into polysilicon can modulate the final Φ_m around the $\Phi_{Mid\text{-}Gap}$ such as in pure nickel silicide without dopant. In other words, a semiconductor has a certain energy level measured by its Fermi level or E_F. An undoped semiconductor has an E_F generally at the middle of the bandgap. N-type doping adjusts the E_F closer to the conduction band while p-type doping moves the E_F nearer the valence band.

There are several examples of FUSI poly gates but the methodology with regard to assembling all processes effectively seems lacking. Moreover, a better design is needed to overcome some performance issues and to enable a lower cost manufacturing process that involves fewer steps.

A recent improvement in the design of transistor devices involves raised source and drain regions which increases the thickness of the source and drain regions available for the silicidation process and lowers sheet resistance of the source and drain regions. An example of elevated source/drain regions that are coplanar with a metal gate electrode is found in U.S. Patent 6,284,609 in which a doped epitaxial growth serves as a raised source/drain region. A metal gate is enclosed on the sides and bottom by oxide liners and a gate dielectric layer, respectively. However, selective epitaxial growth (SEG) requires a separate tool set and the process itself is not easy to perform, thereby increasing manufacturing expense. Additionally, gate formation requires removing a dielectric layer above the channel by an etch process which could damage the substrate below the subsequently formed gate.

In U.S. Patent 6,204,103, a transistor device having fully silicided polysilicon gates and silicided S/D regions is disclosed. One drawback is that the gates and S/D regions are silicided in separate steps that could have different thermal budget allowances and thereby lead to thermal instability and an increase in S/D resistance. Secondly, the gate and S/D regions are not coplanar which could lead to complications during a subsequent etch step that opens contact holes to silicided regions. Moreover, separate masks are required for patterning two different metal layers on the respective gates.

U.S. Patent 5,960,270 describes a MOS transistor in which a metal gate is deposited in an opening above the channel region after silicided S/D regions are formed in the substrate. However, damage to the gate region could easily occur during etching to remove a sacrificial gate. Since the gate region is the most critical portion of a transistor, a gate replacement scheme as disclosed here is questionable in terms of process margin.

U.S. Patent Application 2004/0094804 and a related publication entitled "Issues in NiSi-gated FDSOI device integration", J. Kedzierski, et al., IEDM, 2003, describe fully depleted silicon on insulator (FDSOI) devices with NiSi metal gates. While this approach appears to more closely resemble a full integration flow than other prior art examples, the fabrication still has the disadvantages of separate S/D and gate silicidations, SEG to raise the S/D regions, and non-planar gate and raised S/D regions.

In silicon-on-insulator (SOI) technology, the source/drain regions are formed above an insulator layer, allowing a significant reduction in the source and drain depletion capacitance. On the other hand, for a thin body SOI case, a high series resistance associated with fully silicided source and drain regions and due to the significantly reduced side contact areas, must be overcome before SOI technology is implemented in manufacturing.

In summary, there are several obstacles to implementing fully silicided gates and S/D regions in CMOS technology. Current process flows are too complex and incur extra cost because S/D and gate silicidation occur separately. Note that a gate has a greater thickness than S/D regions which require thinner silicide to avoid S/D junction leakage. Typically, a second (gate) silicidation demands a higher temperature and longer time than S/D silicidation to avoid non-uniform NiSi (phase) formation that causes Φ_m variability. A high thermal budget for the gate silicidation could affect the pre-formed S/D silicide (often NiSi as well) with a resulting Rs increase from silicide agglomeration. When a SEG process is implemented to raise the S/D region, an extra tool and more process time are needed. Even so, the SEG thickness is limited and cannot achieve a level that is coplanar with the gate. Subjecting a thick gate and a thinner raised S/D region to a single silicidation process will likely cause S/D junction

damage. A fourth issue is non-planarity of silicided gate and S/D regions as mentioned previously. A fifth concern is that a SEG raised S/D thickness is limited and even a silicided SEG raised S/D region is not thick enough to separate a subsequently formed Cu contact in a BEOL process flow from an active S/D with sufficient distance.

SUMMARY OF THE INVENTION

One objective of the present invention is to provide a MOSFET structure with a fully silicided gate and S/D regions that are nearly coplanar.

A further objective of the present invention is to provide a MOSFET structure according to the first objective in which the fully silicided gate and S/D regions are separated by a spacer and by a slight recess in the gate below the top of the spacer.

A still further objective of the present invention is to provide a MOSFET structure according to the first objective wherein silicidation stoppers are formed adjacent to the fully silicided gate and S/D regions.

Yet another objective of the present invention is to provide a cost effective method of fabricating fully silicided and nearly planar gate and S/D regions in which selective epitaxial growth (SEG) is not used and the silicidation is performed in a single step.

These objectives are achieved in a first embodiment by providing a substrate such as silicon on which a transistor is to be formed. Optionally, in an SOI embodiment, the substrate may be comprised of an insulating layer with a semiconductor layer formed thereon. In the exemplary embodiment, shallow trench Isolation (STI) regions are formed in the substrate to define an active region. A stack formed by sequentially forming a gate dielectric layer, a polysilicon layer, an oxide hard mask, and a nitride hard mask on the substrate is patterned by conventional photolithography and etching

techniques to fabricate a gate electrode and overlying hard mask above the channel in the active region. A first ion implant is performed to implant a p-type or n-type dopant in the exposed active regions to form source/drain extensions. Next, a spacer comprised of an inner oxide layer and an outer nitride layer is formed on either side of the gate electrode and a second implant is performed followed by activation anneal to form heavily doped source/drain (S/D) elements as contact S/D regions between each spacer and an adjacent isolation region. Thereafter, an insulator layer such as silicon oxide is deposited on the substrate and is selectively patterned to produce an insulator block mask over each STI region. A silicidation stop layer such as Ti/TiN and a conductive layer made of polysilicon, SiGe, SiGeC, or Ge, for example, are sequentially deposited on the insulator block mask and over the entire active region. After a Chemical Mechanical Polish (CMP) process is performed to planarize the partially formed transistor, remove the nitride hard mask, and form raised S/D elements from the conductive layer, the exposed oxide hard mask is removed by an HF dip. Finally, a metal layer such as Ni is deposited on the insulator block mask and transistor region and a silicidation process is employed to fully silicide the gate and raised S/D elements. Unreacted metal is removed to yield a MOSFET with fully silicided gate and raised S/D elements that are nearly coplanar. The fully silicided and raised S/D elements are advantageously bounded on the sides and bottom by silicidation stop layers.

In a second embodiment that represents formation of a Schottky Barrier MOSFET, a gate dielectric layer, gate electrode, and overlying oxide/nitride hard mask with abutting oxide/nitride spacers are formed as in the first embodiment except there are no LDD regions or heavily doped S/D regions in the substrate. An insulator block mask as mentioned earlier is disposed on the STI regions. In this case, the insulator block mask,

spacers, and gate stack serve as an etch mask while a trench is etched in exposed regions of the substrate. Once an overlying photoresist mask above the insulator block mask is removed, a Schottky barrier having a lower metal layer made of Pt, Ni, Co, Ti, Dy, Er, or the like and an upper TiN cap layer is conformally laid down. Thereafter, a conductive layer such as polysilicon is deposited on the insulator block mask and transistor region. A similar sequence as described previously that involves CMP to remove the nitride hard mask, HF dip to remove the oxide hard mask, metal deposition, and silicidation is followed to form a Schottky Barrier MOSFET. The resulting fully silicided gate electrode and S/D elements are nearly coplanar. In this case, the Schottky barrier layer extends into the substrate to allow a thicker silicide layer (raised S/D element) thereon. Thus, vertical S/D engineering is made possible.

The present invention is also a transistor formed by a method of the present invention. The transistor is based on a substrate with STI regions formed therein and is comprised of a fully silicided gate electrode that is nearly coplanar with fully silicided and raised S/D elements. The slightly recessed gate is separated from the raised S/D elements by an oxide/nitride spacer which may be adjusted in width to optimize side capacitance and resistance of the S/D extension region under each spacer. There is an insulator block mask overlying each STI region in the substrate. A silicidation stopper layer is conformally formed along one side of the insulator block mask, above a portion of the S/D region in the substrate, and along the side of the adjacent nitride spacer. For a Schottky Barrier MOSFET, a Schottky barrier layer extends into the substrate and is confined between the tip of the spacer and the tip of the insulator block mask.

BRIEF DESCRIPTION OF THE DRAWINGS

The present invention is illustrated by way of example and not limitation in the accompanying figures, in which like references indicate similar elements, and in which:

FIG. 1 is a cross-sectional view that depicts a partially formed MOSFET with a hard mask above a gate electrode according to one embodiment of the present invention.

FIG. 2 is a cross-sectional view of the structure in FIG. 1 after spacers are added adjacent to the gate and S/D regions are formed in the substrate.

FIG. 3 is a cross-sectional view of the structure in FIG. 2 after an insulator block mask is formed above isolation regions according to the present invention.

FIG. 4 is a cross-sectional view of the structure in FIG. 3 after a silicidation stop layer and conductive layer are deposited on the insulator block mask and active area.

FIG. 5 is a cross-sectional view of the structure in FIG. 4 following a planarization process that forms raised S/D elements and after an etch that removes an oxide hard mask above the gate electrode.

FIG. 6 is a cross-sectional view of the structure in FIG. 5 following deposition of a metal layer on the gate and planarized MOSFET surface.

FIG. 7 is a cross-sectional view of the structure in FIG. 6 after a silicidation is performed and unreacted metal layer is removed to form a fully silicided gate electrode and fully silicided and raised S/D elements.

FIGS. 8 – 12 are cross-sectional views that represent a process of forming a Schottky Barrier MOSFET according to a second embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

The present invention generally relates to semiconductor devices with raised source/drain (S/D) elements and gate electrodes (gates), both of which are fully silicided. More particularly, the invention relates to a MOSFET having a gate that is nearly coplanar with the raised S/D elements and wherein the raised S/D elements are bounded on the sides and bottom by a silicidation stopper layer. The first embodiment illustrated in FIGS. 1 – 7 relates to a MOSFET with conventional lightly doped source/drain (LDD) extension regions and heavily doped S/D contact regions. A second embodiment depicted in FIGS. 8 – 12 represents a Schottky Barrier MOSFET wherein the silicidation stopper layer is a Schottky barrier that extends into the substrate.

Referring to FIG. 1, there is shown a partially formed transistor (MOSFET) **30** that is based on a substrate **10** which may be silicon, silicon-germanium, or another semiconductor material used in the art. Optionally, the substrate **10** may be a silicon (or silicon-germanium, germanium, or any other semiconductor material of interest)-on-insulator (SOI) structure comprised of a stack (not shown) in which a semiconductor layer is formed on an insulator that is disposed on a substructure which may contain active and passive devices as appreciated by those skilled in the art. It is understood that a substrate comprised of more than one device may be referred to as a chip. In SOI technology, the insulator layer is typically silicon oxide and has a thickness from about 100 to 5000 Angstroms while the semiconductor layer has a thickness between about 10 and 1000 Angstroms (or can be thicker as needed).

In the exemplary embodiment, the substrate **10** is comprised of silicon and an n-well or p-well **12** is formed therein by a well known method. Thereafter, isolation regions

such as shallow trench isolation (STI) regions **11** typically made of silicon oxide or a low k dielectric material are formed in the substrate **10** by a conventional process and thereby define the active region of the partially formed MOSFET **30**. STI regions **11** may be coplanar with the substrate **10** as pictured in the drawings, slightly elevated above the substrate, or slightly recessed below the substrate.

A gate stack comprised of a gate dielectric layer **13**, gate layer **14**, silicon oxide layer **15**, and silicon nitride layer **16** is sequentially laid down by a chemical vapor deposition (CVD) method, plasma enhanced CVD (PECVD), or the like. The gate dielectric layer **13** preferably has a thickness of about 5 to 200 Angstroms (in effective oxide thickness, EOT) and may be comprised of one or more of silicon oxide, silicon oxynitride, or silicon nitride. For instance, an EOT of approximately 15 Angstroms is preferred for the 65 nm technology node. Alternatively, gate dielectric layer **13** may be comprised of one or more high k dielectric materials known to those skilled in the art. A high k dielectric material enables an increase in the physical thickness of the gate dielectric layer **13** to suppress tunneling current and prevent a high gate leakage current while maintaining minimum desired EOT. However, a high k dielectric layer generally has a lower thermal stability than silicon oxide, silicon nitride, or silicon oxynitride, and is employed only when subsequent thermal processes may be restricted to temperatures that do not exceed the thermal stability limit of the high k dielectric layer. In an alternative embodiment, the gate dielectric layer **13** is comprised of a high k dielectric layer formed on an interfacial layer that is SiO_2, silicon nitride, or silicon oxynitride.

The gate layer **14** is a conductive material which may be made of doped or undoped polysilicon having a thickness of 300 to 1500 Angstroms and preferably about 500 Angstroms. Silicon oxide layer **15** with a thickness of 100 to 500 Angstroms and

preferably about 300 Angstroms, and silicon nitride layer **16** having a thickness between 100 and 500 Angstroms and preferably about 300 Angstroms, are referred to as hard masks since they protect the gate **14** during subsequent etching and CMP processes. The stack is patterned by conventional lithography and etching techniques that may include a trim etch to form a gate length L_G that is smaller than can be achieved by a lithography method followed by an anisotropic etch. Hereafter, the patterned gate layer is referred to as a gate or gate electrode **14**.

A first ion implant may be performed by a well known method to provide lightly doped source and drain extension (LDD) regions **17** with an appropriate n-type or p-type dopant in substrate **10** between the gate dielectric layer **13** and the STI regions **11**. When the MOSFET **30** is a PMOS type, the channel (not shown) below the subsequently formed gate dielectric layer **13** will have n-type conductivity while the adjacent LDD regions **17** will be comprised of a p-type dopant. Alternatively, the MOSFET **30** may be a NMOS type wherein the channel below the gate dielectric layer **13** has p-type conductivity and adjacent LDD regions **17** have an n-type dopant.

Referring to FIG. 2, a conventional sidewall oxide deposition may be employed to form a silicon oxide layer **18** on the substrate **10** and along the sides of the gate **14**. Thereafter a silicon nitride layer **19** is deposited by a CVD or PECVD technique on the silicon oxide layer **18**. A well known etch process is followed to fabricate an inner oxide spacer **18** and an outer nitride spacer **19** along the gate **14** and above LDD regions **17**. The maximum width of the spacers **18/19** along the top surface of substrate **10** is w_1. Heavily doped S/D regions **20** may then be formed and activated by an appropriate implant between the spacers **18/19** and the adjacent STI region **11** followed by an

anneal and activation process, e.g., furnace anneal, or rapid thermal anneal, or a more advanced laser-anneal, as understood by those skilled in the art.

Referring to FIG. 3, an insulator layer **21** such as a silicon oxide layer with a thickness t_2 of from 500 to 2500 Angstroms is deposited on the transistor region **30** and over the STI regions **11** by a CVD or PECVD method. Note that the thickness t_2 is about equivalent to the thickness of the gate stack (layers **13** – **16**) and is preferably larger than the distance t_1 which represents the combined thickness of the gate dielectric layer **13**, gate **14**, and oxide hardmask **15**. In a preferred embodiment practiced by the inventors, t_2 is about 1100 Angstroms. In an alternative embodiment, the insulator layer may be a composite layer comprised of silicon oxide and silicon nitride or may be a composite of other insulator materials that are compatible with a subsequent patterning process as described in the following section.

A photoresist layer **22** is patterned on the insulator layer **21** and serves as an etch mask while a conventional wet or dry oxide etch is used to remove the exposed insulator layer. The silicon nitride spacer **19** and silicon nitride hard mask **16** protect the silicon oxide hard mask **15** and a substantial portion of the silicon oxide spacer **18**. As a result, the remaining insulator layer is referred to as an insulator block mask **21** that covers the STI regions **11** and may extend slightly over the heavily doped S/D regions **20** to allow for some alignment error. The nitride hard mask **16**, spacers **18/19** and a substantial portion of S/D regions **20** are now uncovered. The insulator block mask **21** advantageously serves as an electrostatic discharge (ESD) mask as well so that a separate ESD masking step is not needed for this invention.

Referring to FIG. 4, the photoresist layer **22** is removed by a standard stripping method and then a cleaning step may be employed to remove any organic residues

from the insulator block mask **21** and transistor region **30**. A silicidation stop layer **23** that is essentially a conformal coating and can also function to control contact resistance is deposited by a CVD, PECVD, or atomic layer deposition (ALD) method on the insulator block mask **21** and transistor region **30** to a thickness of from 30 to 300 Angstroms. Preferably, the silicidation stop layer **23** is a composite comprised of a lower Ti layer and an upper TiN layer. In one embodiment, the lower Ti layer is about 100 Angstroms thick and the upper TiN layer has a thickness of about 200 Angstroms. Optionally, the silicidation stop layer **23** may be comprised of Ni/TiN or Co/TiN. The silicidation stop layer **23** prevents a subsequent silicidation process from reacting with silicon in the substrate **10**. The silicidation stop layer **23** has a vertical section along one side of the insulator block mask and has horizontal sections on the substrate **10**, on the top surface of the insulator block mask **21**, and on the gate stack. The silicidation stop layer **23** also has a curved section along the side of the spacers **18/19**.

In the exemplary embodiment, a conductive layer **24** is formed that fills in the openings between the spacers **18/19** and insulator block mask **21** and has a top surface **25** that is above the level of the uppermost horizontal sections of the silicidation stop layer **23**. The conductive layer **24** may be a polysilicon or amorphous layer that is deposited by a low temperature method at about 400^{o}C to 600^{o}C which is performed using a plasma enhanced CVD process (for lower temperature requirement) or a low pressure CVD process (if compatible for higher temperature requirement). The conductive layer **24** may be doped or undoped. Alternatively, the conductive layer **24** may be comprised of SiGe, SiGeC, or pure Ge in order to modify the mechanical and electrical characteristics of the subsequently formed fully silicided and raised S/D elements to be described in a later section.

Referring to FIG. 5, a conventional CMP process is performed that may involve more than one step to planarize the conductive layer **24** and remove the silicon nitride hardmask **16**. The silicon oxide hard mask **15** serves as a CMP stop to prevent damage to the gate layer **14**. During the CMP process, the horizontal section of the silicidation stop layer **23** above the top surface of the insulator block mask **21** is also removed along with an upper portion of the insulator block mask. The insulator block mask **21**, silicidation stop layer **23**, conductive layer **24**, and spacers **18/19** are now essentially coplanar. The conductive layer **24** over each S/D region **20** is now a raised S/D element and is advantageously formed by a sequence that does not include selective epitaxial growth in order to reduce process complexity and cost. The distance between the gate **14** and raised S/D elements **24** may be increased by lengthening the CMP process time. In other words, the width of silicon nitride spacer **19** on the polished surface of the transistor region **30** becomes greater as the CMP process removes more of insulator block mask **21** and conductive layer **24**.

Next, the gate **14** becomes slightly recessed below the top of the silicon nitride spacer **19** when the MOSFET **30** is subjected to an oxide etch such as a conventional BHF dip that removes the silicon oxide hard mask **15**. At this point, the thickness of the combined silicidation stop layer **23** and conductive layer **24** is from 500 to 700 Angstroms while the gate **14** remains about 500 Angstroms thick. Note that the insulator block mask **21** and silicon oxide spacers **18** may also be thinned to a level that is about coplanar with the gate **14**.

Referring to FIG. 6, a metal layer **26** to be used in a subsequent step to form a metal silicide is deposited by a CVD, ALD, or physical vapor deposition (PVD) method to a thickness of about 100 to 1000 Angstroms on the insulator block mask **21** and on the

transistor region **30**. In one aspect, the metal layer **26** is a composite comprised of Ni and a TiN capping layer and is deposited by a PVD process. Optionally, the metal layer **26** may be comprised of Ni, Co, Pt, Ti, or any other conductive material that can be silicided to give the desired electrical and mechanical properties for a particular device.

In FIG. 7, a silicidation step is carried out by heating the substrate **10** in a furnace with a N_2 or inert gas ambient at a temperature of 200^{O}C to 700^{O}C and preferably at 450^{O}C for about 15 to 30 minutes. Alternatively, a different type of anneal such as a conventional rapid thermal anneal (RTA) at a temperature of 200^{O}C to 700^{O}C for 10 to 120 seconds may be performed, depending on the desired characteristics of the silicide and integration limitations. It should be understood that the temperature used for the silicidation process depends upon the conductive material to be silicided. For instance, Ni requires a lower temperature than Ti. The gate **14** is transformed into a fully silicided gate electrode **27** and the conductive layer **24** is converted to a fully silicided and raised S/D element **28** on each side of the gate stack. Following the silicidation, unreacted metal layer **26** is selectively removed by a well known method such as treatment with a H_2SO_4/H_2O_2 solution at 130^{O}C for about 10 minutes. The formation of the transistor **30** is now essentially complete. Note that a standard process may follow such as a pre-metal dielectric (PMD) deposition. A PMD deposition is typically performed before any contact/metal formation.

One advantage of the method and structure of the present invention is that the fully silicided and raised S/D layer **28** is thicker than in prior art and thereby allows a copper backend of the line (BEOL) process flow to immediately follow. For instance, a silicon nitride layer (not shown) about 300 Angstroms thick may be deposited on the insulator block mask **21** and transistor region **30** to function as a Cu seal layer and etch stop

layer during subsequent processing that forms contacts to the silicided regions. Thus, an extra process used in the prior art to form a W plug on S/D elements to increase the effective metal thickness before forming a silicon nitride or Cu seal layer in a Cu BEOL fabrication is no longer needed.

Another advantage of the first embodiment is that the present invention provides a MOSFET having a fully silicided gate and fully silicided and raised S/D elements that are about coplanar and thereby allows a wider process margin in a subsequent step that forms contacts to the silicided elements. For example, an etch to form contact holes can easily punch through into the S/D regions of the substrate when a shallow raised S/D element or no raised S/D element is employed. Furthermore, silicidation of the gate and raised S/D elements is accomplished in a single step that avoids process incompatibility associated with prior art methods that require two different silicidation steps. In the present invention, gate silicidation is controlled in both horizontal and vertical directions by spacers and the gate dielectric layer, respectively, while silicidation of raised S/D regions is controlled by a silicidation stop layer.

The silicidation stop layer is advantageously used in the first embodiment to enable a shallower S/D region in the substrate than was previously possible because in the present invention no silicon is lost from the substrate during silicidation. Thus, an ultra shallow S/D region can be achieved without a sheet resistance (Rs) penalty. The overall process is highly flexible since the fully silicided gate is compatible with high k gate dielectric layers and can be tuned for Φ_m and threshold voltage (Vth) control by appropriate gate doping prior to silicidation.

The present invention is also the MOSFET structure **30** otherwise known as a transistor shown in FIG. 7 that is comprised of a substrate **10** and a fully silicided gate

27 and fully silicided and raised S/D elements **28** that are nearly coplanar. The substrate **10** may be silicon and may be based on a SOI design that includes an insulating layer and overlying semiconductor layer that are formed on a substructure comprised of one or more other devices. The substrate **10** includes isolation regions **11**, a channel (not shown) that has a certain conductivity type (n or p), S/D regions **20**, and LDD regions **17** adjacent to the channel which have a conductivity type opposite to that of the channel. The transistor **30** further includes a gate dielectric layer **13** formed over the channel, a fully silicided gate electrode **27** on the gate dielectric layer, spacers **18/19** with a side and top surface formed adjacent to the sides of the gate electrode, and raised source/drain elements **28** that are fully silicided and bounded on the sides and bottom by a silicidation stop layer **23**.

There is a vertical section of the silicidation stop layer **23** that abuts a side of the insulator block mask **21**. The insulator block mask is comprised of two sides and a top surface and is formed above isolation regions **11**. Another section of the silicidation stop layer **23** abuts the curved side of the silicon nitride spacer **19**. There is a horizontal section of the silicidation stop layer **23** formed on the substrate on the S/D regions **20**. The fully silicided gate **27** is slightly recessed below the top surface of the silicon nitride spacers **19** and fully silicided, raised S/D elements **28** by a distance of about 100 to 300 Angstroms.

The remaining aspects of elements in transistor **30** were previously described. The advantages of the transistor **30** are the same as those mentioned with respect to the first embodiment. Note that the lateral width of the spacers **18/19** between the fully silicided gate **27** and silicidation stop layer **23** may be increased to optimize side capacitance.

In an embodiment where the substrate comprises an SOI structure, the method of the present invention improves process yield and reduces contact resistance since the silicidation stopper layers prevent silicon loss from an ultra thin top semiconductor layer in the SOI substrate during the silicidation of the raised S/D elements.

In a second embodiment of the present invention, a Schottky Barrier MOSFET is fabricated according to the process flow depicted in FIGS. 8 – 12. The partially formed transistor **40** differs from the previously described transistor **30** in FIG. 2 in that both the LDD regions **17** and heavily doped S/D regions **20** are omitted. This means that all the ion implantation in the first embodiment is omitted in the second embodiment. Furthermore, a trench **31** is formed in the substrate (FIG. 9) between the insulator block mask **21** and horizontal section of silicon oxide spacer **18** and a Schottky barrier layer **33** (FIG. 10) replaces the silicidation stop layer **23** that was used in the first embodiment.

All of the elements in FIG. 8 have been described previously and were formed according to the process sequence in the first embodiment except that no ion implantation was performed and LDD regions **17** and heavily doped S/D regions **20** are omitted. In the preferred embodiment, the maximum width w_2 of the spacers **18/19** is about one half of w_1 (FIG. 2) and is determined by the allowable resistance under the spacer region and by the allowable distance between the tips of the channel to the tips of the silicide formed in a subsequent step.

Referring to FIG. 9, an insulator block mask **21** with a thickness t_2 is formed by using a patterned photoresist layer **22** as an etch mask as described previously. It should be understood that one or more other insulator materials besides silicon oxide may be used to form an insulator block mask **21** as indicated in the first embodiment. Again, t_2

is preferably greater than t_1 which is the combined thickness of the gate dielectric layer **13**, gate layer **14**, and silicon oxide hard mask **15**. The process sequence in the second embodiment differs from that in the first embodiment by adding an additional step wherein the photoresist layer **22**, insulator block mask **21**, and spacers **18/19** serve as an etch mask while a conventional etch process is employed to remove exposed portions of substrate **10**. For example, a chlorine based reactive ion etch may be used to remove silicon from substrate **10**. A source and drain (S/D) **31** which is a trench having a depth **d** of from 0 to 100 Angstroms and preferably less than 50 Angstroms is formed in substrate **10** between insulator block mask **21** and adjacent spacers **18/19**.

Referring to FIG. 10, the photoresist layer **22** is stripped by a conventional method and then a cleaning step may be performed to remove any organic residues on the insulator block mask **21** or in transistor region **40**. A key step is now performed which is deposition of a Schottky barrier **33** by a CVD, PECVD, or ALD method, or by a combination of two or more of the aforementioned techniques. In one embodiment, the Schottky barrier **33** is a composite layer having a lower metal layer comprised of Ni about 50 to 100 Angstroms thick and an upper TiN cap layer with a thickness of about 100 to 300 Angstroms. Alternatively, the Schottky metal layer may be comprised of Pt, Co, Dy, Er, or Ti as appreciated by those skilled in the art. Note that the Schottky barrier **33** preferably covers the S/D **31** and is generally conformal to side and top surface of the insulator block mask **21** and to the transistor region **40** on which it is formed. In other words, the Schottky barrier **33** has a vertical section along the side of the insulator block mask **21** and has horizontal sections on the top surface of the insulator block mask, in the S/D **31**, and on the top surface of the spacers and gate

stack. Moreover, the Schottky barrier **33** conforms to the curved side of the silicon nitride spacers **19**

Thereafter, a conductive layer **34** is deposited on the Schottky barrier **33** by using a low temperature method similar to the one mentioned with respect to conductive layer **24** in the first embodiment. Preferably, the conductive layer **34** is polysilicon but optionally may be SiGe, SiGeC, or Ge. Conductive layer **34** has a top surface **35** that is at a higher level than the uppermost horizontal sections of the Schottky barrier **33**.

Referring to FIG. 11, a conventional CMP process is performed that may involve more than one step to planarize the conductive layer **34** and remove the silicon nitride hardmask **16**. The silicon oxide hard mask **15** serves as a CMP stop to prevent damage to the gate **14**. During the CMP process, the horizontal sections of the Schottky barrier **33** on the top surfaces of the insulator block mask **21**, spacers **18/19**, and gate stack are also removed along with upper portions of the insulator block mask and spacers **18/19**. The insulator block mask **21**, Schottky barrier **33**, conductive layer **34**, and spacers **18/19** are now essentially coplanar. The conductive layer **34** is now a raised S/D element over the Schottky barrier **33** in the S/D **31** on either side of the gate stack. Note that the raised S/D elements **34** are advantageously formed by a sequence that does not include selective epitaxial growth in order to reduce process complexity and cost. In the next step, the gate **14** becomes slightly recessed below the top of the spacers **18/19** when the partially formed Schottky Barrier MOSFET **40** is subjected to an oxide etch such as a conventional BHF dip that removes the silicon oxide hard mask **15** and top portions of the insulator block mask **21** and silicon oxide spacer **18**. At this point, the combined thickness of the Schottky barrier **33** and raised S/D element **34** on

either side of the gate **14** is from 500 to 700 Angstroms while the gate remains about 500 Angstroms thick.

Referring to FIG. 12, the previously described sequence of depositing a metal layer (not shown) on an insulator block mask **21** and adjacent transistor region, performing a silicidation, and selectively removing unreacted metal layer is followed to afford the essentially complete Schottky Barrier MOSFET **40**. When the metal layer is Ni having a thickness of 100 to 1000 Angstroms, the silicidation conditions are the same as provided in the first embodiment. Moreover, the same H_2SO_4/H_2O_2 treatment described in the first embodiment may be used to remove unreacted metal layer. As a result, a fully silicided and raised S/D element **36** is formed on either side of a fully silicided gate electrode **37**. The fully silicided and raised S/D element **36** is formed on the Schottky barrier **33** between an insulator block mask **21** and adjacent spacers **18/19**.

The advantages of the second embodiment are the same as mentioned for the first embodiment with an additional benefit that no sacrifice is expected in S/D resistance because the raised S/D element is metallic and extends from the top of the spacers to the substrate. Thus, the second embodiment possesses the additional advantage of vertical engineering wherein the thickness of the raised S/D regions may be adjusted by varying the depth **d** (FIG. 9) of the S/D **31** and the thickness of Schottky barrier **33**. In this case, the Schottky barrier prevents silicon loss from the substrate during the silicidation process to enable shallower S/D regions in the substrate than are achieved in prior art.

The present invention is also the Schottky Barrier MOSFET **40** shown in FIG. 12 that is comprised of a substrate **10**, and a fully silicided gate **37** and fully silicided and raised S/D elements **36** that are nearly coplanar. Schottky Barrier MOSFET **40** differs from the

first embodiment (transistor **30**) in that the LDD extensions **17** and heavily doped regions **20** are omitted in substrate **10**. Additionally, the silicidation stop layer in the first embodiment is replaced by a Schottky barrier **33** that extends into the substrate and allows the thickness of the overlying raised S/D elements **36** to be adjusted. As indicated previously, the advantages of the Schottky Barrier MOSFET are the same as those mentioned with respect to the first embodiment. Additionally, thicker raised S/D elements may be formed to make electrical contact with subsequently formed devices.

While this invention has been particularly shown and described with reference to, the preferred embodiments thereof, it will be understood by those skilled in the art that various changes in form and details may be made without departing from the spirit and scope of this invention.

We claim:

1. A fully salicided MOSFET structure, comprising:

(a) a substrate having a channel bounded by doped source/drain (S/D) regions that are formed in an active area defined by isolation regions;

(b) a patterned gate stack with two sides formed on said substrate wherein each side is abutted by a spacer having a top surface and a side, said gate stack is comprised of a gate dielectric layer formed on the substrate above the channel and an overlying and fully silicided gate electrode which is recessed below the top surface of the spacers by a certain distance;

(c) an insulator block mask having two sides and a top surface which is formed on the substrate above the isolation regions;

(d) a silicidation stop layer with a first thickness that is formed adjacent to one side of the insulator block mask, on the S/D region of the substrate between the insulator block mask and a spacer, and along the side of the spacer; and

(e) a raised and fully silicided S/D element formed on the silicidation stop layer on either side of the fully silicided gate electrode and having a top surface that is essentially coplanar with the top surface of the spacers.

2. The MOSFET structure of claim 1 wherein a spacer is comprised of an inner silicon oxide layer that abuts the gate stack and an outer silicon nitride layer formed on the inner silicon oxide layer.

3. The MOSFET structure of claim 1 wherein the fully silicided gate electrode

and fully silicided and raised S/D elements are comprised of nickel silicide (NiSi), silicides of SiGe, SiGeC, or Ge.

4. The MOSFET structure of claim 1 wherein the insulator block mask is comprised of silicon oxide, a composite of silicon oxide and silicon nitride, or a composite of insulator materials that are compatible with a patterning process used to form the insulator block mask.

5. The MOSFET structure of claim 1 wherein the silicidation stop layer is a composite layer comprised of a TiN layer on a Ti layer.

6. The MOSFET structure of claim 1 wherein the silicidation stop layer is essentially a conformal layer and has a thickness between about 30 and 300 Angstroms.

7. The MOSFET structure of claim 1 wherein the fully silicided gate electrode is doped to adjust the Φ_m and Vth.

8. The MOSFET structure of claim 1 wherein the substrate is based on SOI technology and is comprised of an upper semiconductor layer formed on an insulator layer.

9. The MOSFET structure of claim 1 wherein the certain distance that the fully silicided gate electrode is recessed below the spacers is from about 100 to 300 Angstroms.

10. A fully salicided Schottky Barrier MOSFET, comprising:

(a) a substrate having a channel bounded by an active area defined by isolation regions;

(b) a patterned gate stack with two sides formed on said substrate wherein each side is abutted by a spacer having a top surface and a curved side, said gate stack is comprised of a gate dielectric layer formed on the substrate above the channel, and an overlying and fully silicided gate electrode which is recessed below the top surface of the spacers by a certain distance;

(c) an insulator block mask having two sides and a top surface which is formed on the substrate above the isolation regions;

(d) a trench having a certain depth formed in the substrate between a side of an insulator block mask and the curved side of a spacer;

(e) a Schottky barrier layer with a first thickness that is formed adjacent to one side of the insulator block mask, in the recess between the insulator block mask and a spacer, and along the curved side of a spacer; and

(f) a raised and fully silicided S/D element formed on the Schottky barrier layer on either side of the fully silicided gate electrode and having a top surface that is essentially coplanar with the top surface of the spacers.

11. The Schottky Barrier MOSFET of claim 10 wherein a spacer is comprised of an inner silicon oxide layer that abuts the gate stack and an outer silicon nitride layer formed on the inner silicon oxide layer.

12. The Schottky MOSFET of claim 10 wherein the fully silicided gate

electrode is comprised of nickel silicide (NiSi) and the fully silicided and raised S/D elements are comprised of Ni and Si, SiGe, or SiGeC, or Ni and Ge.

13. The Schottky Barrier MOSFET of claim 10 wherein the insulator block mask is comprised of silicon oxide, a composite of silicon oxide and silicon nitride, or a composite of insulator materials that are compatible with a patterning process that forms the insulator block mask.

14. The Schottky Barrier MOSFET of claim 10 wherein the Schottky barrier layer is a composite layer having a lower metal layer comprised of Ni, Pt, Co, Dy, Er, or Ti and an upper TiN capping layer.

15. The Schottky Barrier MOSFET of claim 14 wherein the Schottky barrier layer is a conformal layer wherein the lower metal layer is about 50 to 100 Angstroms thick and the upper TiN cap layer has a thickness of about 100 to 300 Angstroms.

16. The Schottky Barrier MOSFET of claim 10 wherein the fully silicided and raised S/D elements and the fully silicided gate layer are doped to adjust the work function (Φ_m).

17. The Schottky Barrier MOSFET of claim 10 wherein the substrate is based on SOI technology and is comprised of an upper semiconductor layer formed on an insulator layer.

18. The Schottky Barrier MOSFET of claim 10 wherein the certain distance that the fully silicided gate electrode is recessed below the spacers is from about 100 to 300 Angstroms.

19. The Schottky Barrier MOSFET of claim 10 wherein the certain depth of the trench in the substrate is from about 0 to 100 Angstroms.

20. The Schottky Barrier MOSFET of claim 10 further comprised of a silicon nitride or copper seal layer formed on the insulator block mask, spacers, fully silicided gate electrode, and on the fully silicided and raised S/D elements.